OT 15 2001 & DIT 16 2001 &

10/29/0/ Hayes
Attorney Docket No.: SEL-173

THE UNITED SEATES PATENT AND TRADEMARK OFFICE

In re Application of: )	
Ohtani et al. )	I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:
Serial No.: 09/535,836 )	Commissioner for Patents, Washington, D.C. 20231 on October 12, 2001
Filed: March 28, 2000 )	Signature P. H. William
For: Semiconductor Device ) and the Fabricating ) Method Thereof )	Name Bobbi Wilson

AMENDMENT

Commissioner for Patents Washington, D.C. 20231

2811

H. Vu

Sir:

Art Group:

Examiner:

Please amend the above-identified application as follows:

## IN THE SPECIFICATION:

Please amend the title to read as follows:

Semiconductor Device Having Multi-layer Wiring

## IN THE CLAIMS:

Please amend claims 1, 7, 19, 28 and 34 as follows:

1. (Amended) A semiconductor/device comprising:

a first insulating film comprising an organic material formed over a conductive layer;

a first metallic layer formed on said first insulating film;

01 FC:103 02 FC:102 108.00 OP 84.00 OP